



Very Low Power 4-Output PCle Clock Buffer With On-Chip Termination

Features

- → 3.3V supply voltage
- → HCSL input: 100MHz, also support 50MHz, 125MHz or 133.33MHz via SMBus
- → 4 differential low power HCSL outputs with on-chip termination
- → Default $Z_{OUT} = 85Ω$
- → Spread spectrum tolerant
- → Individual output enable
- → Programmable Slew rate and output amplitude for each output
- → Differential outputs blocked until PLL is locked
- → Strapping pins or SMBus for configuration
- → Differential output-to-output skew <50ps
- → Very low jitter outputs
 - ♦ Differential cycle-to-cycle jitter <50ps
 - ♦ PCIe Gen1/Gen2/Gen3/Gen4/Gen5 CC compliant
 - ♦ PCIe Gen 2 and 3 SRiS and SRnS compliant
- → Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- → Halogen and Antimony Free. "Green" Device (Note 3)
- → For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

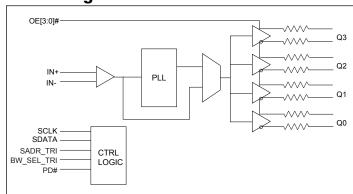
- → Packaging (Pb-free & Green):
 - ♦ 32-lead 5×5mm TQFN

Description

The PI6CB33402 is a 4-output very low power PCIe Gen1/Gen2/Gen3/Gen4/Gen5 clock buffer. It takes a reference input to fanout four 100MHz low power differential HCSL outputs with on-chip terminations. The on-chip termination can save 16 external resistors and make layout easier. Individual OE pin for each output provides easier power management.

It uses Diodes proprietary PLL design to achieve very low jitter that meets PCIe Gen1/Gen2/Gen3/Gen4/Gen5 requirements. Other than PCIe 100MHz support, this device also support Ethernet application with 50MHz, 125MHz and 133.33MHz via SMBus. It provides various options such as different slew rate and amplitude through SMBUS so that users can configure the device easily to get the optimized performance for their individual boards.

Block Diagram



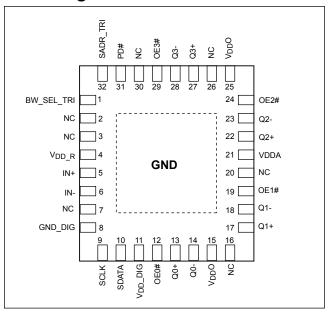
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.





Pin Configuration



Pin Description

Pin Number	Pin Name	Ту	pe	Description
1	BW_SEL_TRI	Input	Tri-level	Latch to select low loop bandwidth, bypass PLL, and high loop bandwidth. This pin has both internal pull-up and pull-down
2	NC			Internal connected for feedback loop. Do not connect this pin
3	NC			Internal connected for feedback loop. Do not connect this pin
4	V _{DD} _R	Power		Power supply for input differential buffers
5	IN+	Input		Differential true clock input
6	IN-	Input		Differential complementary clock input
7	NC			Do not connect this pin
8	GND_DIG	Power		Ground for digital circuitry
9	SCLK	Input	CMOS	SMBUS clock input, 3.3V tolerant
10	SDATA	Input/ Output	CMOS	SMBUS Data line, 3.3V tolerant
11	V _{DD} _DIG	Power		Power supply for digital circuitry, nominal 3.3V
12	OE0#	Input	CMOS	Active low input for enabling Q0 pair. This pin has an internal pull-down. $1 = $ disable outputs, $0 = $ enable outputs
13	Q0+	Output	HCSL	Differential true clock output
14	Q0-	Output	HCSL	Differential complementary clock output
15, 25	V_{DDO}	Power		Power supply for differential outputs
16	NC			Do not connect this pin
17	Q1+	Output	HCSL	Differential true clock output
18	Q1-	Output	HCSL	Differential complementary clock output





Pin Description Cont.

Pin Number	Pin Name	Ту	pe	Description
19	OE1#	Input	CMOS	Active low input for enabling Q1 pair. This pin has an internal pull-down. 1 = disable outputs, 0 = enable outputs
20	NC			Do not connect this pin
21	V_{DDA}	Power		Power supply for analog circuitry
22	Q2+	Output	HCSL	Differential true clock output
23	Q2-	Output	HCSL	Differential complementary clock output
24	OE2#	Input	CMOS	Active low input for enabling Q2 pair. This pin has an internal pull-down. 1 = disable outputs, 0 = enable outputs
26	NC			Do not connect this pin
27	Q3+	Output	HCSL	Differential true clock output
28	Q3-	Output	HCSL	Differential complementary clock output
29	OE3#	Input	CMOS	Active low input for enabling Q3 pair. This pin has an internal pulldown. 1 = disable outputs, 0 = enable outputs
30	NC			Do not connect this pin
31	PD#	Input	CMOS	Input notifies device to sample latched inputs and start up on first high assertion. Low enters Power Down Mode, subsequent high assertions exit Power Down Mode. This pin has internal pull-up resistor.
32	SADR_TRI	Input	Tri-level	Latch to select SMBus Address. This pin has an internal pull-down
	EPAD	Power		Connect to Ground





SMBus Address Selection Table

	SADR	Address	+Read/Write Bit
	0	1101011	X
State of SADR on first application of PD#	M	1101100	X
	1	1101101	X

Power Management Table

PD#	IN	SMBus OE bit	OEn#	Qn+	Qn-	PLL Status
0	X	X	X	Low ⁽²⁾	Low ⁽²⁾	Off
1	Running	0	X	Low ⁽²⁾	Low ⁽²⁾	On ⁽¹⁾
1	Running	1	0	Running	Running	On ⁽¹⁾
1	Running	1	1	Low ⁽²⁾	Low ⁽²⁾	On ⁽¹⁾

Note:

PLL Operating Mode Select Table

BW_SEL_TRI	Operating Mode	Byte1 [7:6] Readback	Byte1 [4:3] Control
0	PLL with low Bandwidth	00	00
M	PLL Bypass	01	01
1	PLL with high Bandwidth	11	11

Frequency Select table

Freq. Select Byte 3 [4:3]	IN (MHz)	Qn (MHz)
00 (default)	100	100
01	50	50
10	125	125
11	133.33	133.33

4

^{1.} If PLL Bypass mode is selected, the PLL will be off and outputs will be running.

^{2.} The output state is set by B11[1:0] (Low/Low default)





Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature65°C to +150°C
Supply Voltage to Ground Potential, V_{DDxx} 0.5V to +4.6V
Input Voltage $-0.5V$ to $V_{DD+0.5V}$, not exceed 4.6V
SMBus, Input High Voltage
ESD Protection (HBM)
Junction Temperature

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Operating Conditions

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
$V_{\mathrm{DDO}},$ $V_{\mathrm{DDA}},$ $V_{\mathrm{DD}}R,$ $V_{\mathrm{DD}}DIG$	Power Supply Voltage		3.135	3.3	3.465	V
I_{DDA}	Analog Power Supply Current	V_{DDA} , PLL mode, All outputs active @100MHz		21	25	mA
I _{DD_DIG}	Supply Current for V _{DD_DIG}	V _{DD_DIG} , All outputs active @100MHz		0.1	1	mA
I_{DDO_R}	Power Supply Current for Outputs ⁽²⁾	V_{DDO}, V_{DD_R} , PLL mode, All outputs active @100MHz		48	54	mA
I _{DDA_PD}	Analog Power Supply Power Down ⁽¹⁾ Current	V_{DDA} , PLL mode, All outputs LOW/LOW		0.5	1	mA
I _{DD_DIG_PD}	Power Supply Power Down ⁽¹⁾ Current for V _{DD_DIG}	V _{DD_DIG} , All outputs LOW/LOW		0.1	1	mA
I _{DDO_R_PD}	Power Supply Current Power Down ⁽¹⁾ for Inputs and Outputs	V_{DDO} , $V_{\mathrm{DD_R}}$ All outputs LOW/LOW		1	2	mA
$T_{\mathbf{A}}$	Ambient Temperature	Industrial grade	-40		85	°C

Note:

- 1. Input clock is not running.
- 2. Outputs drive 5 inch trace.

Input Electrical Characteristics

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
R _{pu}	Internal pull up resistance			120		ΚΩ
R _{dn}	Internal pull down resistance			120		ΚΩ
L _{PIN}	Pin inductance				7	nН





SMBus Electrical Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
V _{DDSMB}	Nominal bus voltage		2.7		3.6	V
		SMBus, V _{DDSMB} = 3.3V	2.1		3.6	
V_{IHSMB}	SMBus Input High Voltage	SMBus, V _{DDSMB} < 3.3V	0.65 V _{DDSMB}			V
37	SMBus Input Low Voltage	SMBus, V _{DDSMB} = 3.3V			0.8	V
V_{ILSMB}		SMBus, V _{DDSMB} < 3.3V			0.8	
I _{SMBSINK}	SMBus sink current	SMBus, at V _{OLSMB}	4			mA
V_{OLSMB}	SMBus Output Low Voltage	SMBus, at I _{SMBSINK}			0.4	V
f_{MAXSMB}	SMBus operating frequency	Maximum frequency			500	kHz
t _{RMSB}	SMBus rise time	(Max V _{IL} - 0.15) to (Min V _{IH} + 0.15)			1000	ns
t _{FMSB}	SMBus fall time	(Min V _{IH} + 0.15) to (Max V _{IL} - 0.15)			300	ns

LVCMOS DC Electrical Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
V _{IH}	Input High Voltage	Single-ended inputs, except SMBus	0.75 V _{DD}		V _{DD} +0.3	V
V _{IM}	Input Mid Voltage	SADR_TRI, BW_SEL_TRI	$0.4 \mathrm{V}_\mathrm{DD}$	$0.5 \mathrm{V}_\mathrm{DD}$	$0.6 V_{ m DD}$	V
V_{IL}	Input Low Voltage	Single-ended inputs, except SMBus	-0.3		0.25 V _{DD}	V
I_{IH}	Input High Current	Single-ended inputs, $V_{IN} = V_{DD}$			5	μΑ
I_{IL}	Input Low Current	Single-ended inputs, $V_{IN} = 0V$	-5			μΑ
I_{IH}	Input High Current	Single-ended inputs with pull up / pull down resistor, $V_{IN} = V_{DD}$			50	μА
I_{IL}	Input Low Current	Single-ended inputs with pull up / pull down resistor, $V_{\rm IN}$ = 0V	-50			μΑ
C _{IN}	Input Capacitance		1.5		5	pF





LVCMOS AC Electrical Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
t _{OELAT}	Output enable latency	Q start after OE# assertion Q stop after OE# deassertion	1		3	clocks
t _{PDLAT}	PD# de-assertion	Differential outputs enable after PD# deassertion		20	300	us

HCSL Input Characteristics(1)

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
V _{IHDIF}	Diff. Input High Voltage ⁽³⁾	IN+, IN-, single-end measurement	600	800	1150	mV
V_{ILDIF}	Diff. Input Low Voltage ⁽³⁾	IN+, IN-, single-end measurement	-300	0	300	mV
V_{COM}	Diff. Input Common Mode Voltage		150		900	mV
V _{SWING}	Diff. Input Swing Voltage	Peak to peak value (V _{IHDIF} - V _{ILDIF)}	300		2900	mV
f_{INBP}	Input Frequency	PLL Bypass mode	1		200	MHz
f _{IN100}	Input Frequency	100MHz PLL	99.9	100	100.1	MHz
f _{IN133}	Input Frequency	133MHz PLL	133.2	133.33	133.46	MHz
f _{IN125}	Input Frequency	125MHz PLL	124.87	125	125.12	MHz
f _{IN50}	Input Frequency	50MHz PLL	49.95	50	50.05	MHz
f _{MODI} - PCIe	Input SS Modulation Freq. PCIe	Allowable frequency for PCIe applications (Triangular Modulation)	30		33	kHz
f _{MODIN} -	Input SS Modulation Freq. non-PCIe	Allowable frequency for non-PCIe applications (Triangular Modulation)	0		46	kHz
t _{STAB}	Clock stabilization	From $V_{\rm DD}$ Power-Up and after input clock stabilization or de-assertion of PD# to 1st clock		0.75	1.0	ms
t _{RF}	Diff. Input Slew Rate ⁽²⁾	Measured differentially	0.4			V/ns
I _{IN}	Diff. Input Leakage Current	$V_{IN} = V_{DD}, V_{IN} = GND$	-5	0.01	5	uA
t_{DC}	Diff. Input Duty Cycle	Measured differentially	45		55	%
tj _{c-c}	Diff. Input Cycle to cycle jitter	Measured differentially			125	ps

Note:

- 1. Guaranteed by design and characterization, not 100% tested in production
- 2. Slew rate measured through +/-75mV window centered around differential zero
- $3. \ The device can be driven by a single-ended clock by driving the true clock and biasing the complement clock input to the V bias, where V bias is (V_{IH}-V_{IL})/2$





HCSL Output Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Condition	Min.	Тур.	Max.	Units
V _{OH}	Output Voltage High ⁽¹⁾	Statistical measurement on single-ended	660	784	850	mV
V _{OL}	Output Voltage Low ⁽¹⁾	signal using oscilloscope math function	-150		150	mV
V _{OMAX}	Output Voltage Maximum ⁽¹⁾	Measurement on single ended signal using		816	1150	mV
V _{OMIN}	Output Voltage Minimum ⁽¹⁾	absolute value	-300	-42		mV
V _{OC}	Output Cross Voltage(1,2,4)		250	430	550	mV
DV _{OC}	V _{OC} Magnitude Change ^(1,2,5)			12	140	mV

Note:

- 1. At default SMBUS amplitude settings
- 2. Guaranteed by design and characterization, not 100% tested in production
- 3. Measured from differential waveform
- 4. This one is defined as voltage where Q+ = Q- measured on a component test board and only applied to the differential rising edge
- $5. \ The \ total \ variation \ of \ all \ Vcross \ measurements \ in \ any \ particular \ system. \ This \ is \ a \ subset \ of \ Vcross_min/max \ allowed.$

HCSL Output AC Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Condition	Min.	Тур.	Max.	Units
f _{OUT}	Output Frequency		50	100	133.33	MHz
DIAZ	PLL bandwidth ^(1,8)	-3dB point in High Bandwidth Mode	1.3	3.2	3.6	MHz
BW	PLL bandwidtn	-3dB point in Low Bandwidth Mode	0.7	1.7	1.9	MHz
tj _{peak}	PLL Jitter Peaking	Peak pass band gain		0.8	2	dB
_	Slew rate ^(1,2,3)	Scope averaging on fast setting	2.5	3.2	4.0	V/ns
t _{RF}	Siew rate	Scope averaging on slow setting	2.2	3.0	3.7	V/ns
Dt _{RF}	Slew rate matching ^(1,2,4)	Scope averaging on		7	15	%
t _{SKEW}	Output Skew ^(1,2)	Averaging on, $V_T = 50\%$		21	50	ps
	D (1.1)	PLL Bypass mode, $V_T = 50\%$	2000	2500	3000	ps
t _{PDELAY}	Propagation delay	PLL mode, $V_T = 50\%$	-200	90	200	ps
t_{DC}	Duty Cycle ^(1,2)	Measured differentially, PLL Mode	45	50	55	%
t _{DCD}	Duty Cycle Distortion ^(1,7)	Measured differentially, PLL Bypass Mode at 100MHz	-3.5	0	3.5	%
t _{DCD}	Duty Cycle Distortion ^(1,7)	Measured differentially, SE input, PLL Bypass Mode at 100MHz	-10	0	10	%
	(1.2)	PLL mode		14	50	ps
tj _{c-c}	Cycle to cycle jitter ^(1,2)	Additive jitter, Bypass mode		0.1	1	ps





HCSL Output AC Characteristics (jitter)

Symbol	Parameters	Condition	Min.	Тур.	Max.	Spec Limit	Units
		PCIe Gen 1 ⁽⁶⁾		25	35	86	ps(p-p)
		PCIe Gen 2 Low Band, 10kHz < f < 1.5MHz		0.6	0.8	3	ps
		PCIe Gen 2 High Band, 1.5MHz < f < Nyquist (50MHz)		0.7	1.2	3.1	ps
	Integrated phase jitter PLL	PCIe Gen 3 (PLL BW of 2-4 or 2-5MHz, CDR =10MHz)		0.25	0.4	1	ps
tjphasepll	mode (RMS) ^(1,5)	PCIe Gen 4 (PLL BW of 2-4 or 2-5MHz, CDR =10MHz)		0.25	0.4	0.5	ps
		PCIe Gen 5 (PLL BW of 500k to 1.8MHz. CDR =20MHz) ⁽¹¹⁾		0.07	0.12	0.15	ps
		125MHz, 1.5MHz to 20MHz, -20dB/ decade Rollover < 1.5MHz, -40dB/de- cade rolloff > 10MHz	0.3		ps		
		133.33MHz		0.15	0.3		ps
		PCIe Gen 1		0.01	0.05		ps(p-p)
		PCIe Gen 2 Low Band, 10kHz < f < 1.5MHz		0.01	0.05		ps
		PCIe Gen 2 High Band, 1.5MHz < f < Nyquist (50MHz)		0.01	0.05		ps
		PCIe Gen 3 (PLL BW of 2-4 or 2-5MHz, CDR =10MHz)		0.01	0.05		ps
tjphasea	Additive Integrated phase jitter (RMS) ^(1,5,10)	PCIe Gen 4 (PLL BW of 2-4 or 2-5MHz, CDR =10MHz)		0.01	0.05		ps
		PCIe Gen 5 (PLL BW of 500k to 1.8MHz. CDR =20MHz) ⁽¹¹⁾		0.01	0.05		ps
		125MHz, 1.5MHz to 20MHz, -20dB/ decade Rollover < 1.5MHz, -40dB/de- cade rolloff > 10MHz		0.01	0.05		ps
		133.33MHz		0.01	0.05		ps
		156.25MHz 12k to 20MHz		0.01	0.05		ps

Note:

- 1. Guaranteed by design and characterization, not 100% tested in production
- 2. Measured from differential waveform
- $3. \ Slew\ rate\ is\ measured\ through\ the\ Vswing\ voltage\ range\ centered\ around\ differential\ 0V,\ within\ +/-150mV\ window$
- $4. \ Slew\ rate\ matching\ is\ measured\ through\ +/-75mV\ window\ centered\ around\ differential\ zero$
- 5. See http://www.pcisig.com for complete specs
- 6. Sample size of at least 100k cycles. This can be extrapolated to 108ps pk-pk @ 1M cycles for a BER of 10^{-12}
- 7. Duty cycle distortion is the difference in duty cycle between the output and input clock when the device is operated in the PLL bypass mode
- 8. The Min and Max values of each BW setting track each other, low BW max will never occur with high BW min
- 9. Applies to all differential outputs
- 10. For additive jitter RMS value is calculated by the following equation = SQRT [(total jitter)*2 (input jitter)*2]
- 11. PCIe Gen 5 v0.9 specification





SMBus Serial Data Interface

PI6CB33402 is a slave only device that supports block read and block write protocol using a single 7-bit address and read/write bit as shown below.

Read and write block transfers can be stopped after any complete byte transfer.

Address Assignment

A6	A5	A4	A3	A2	A1	A0	R/W
1	1	0	1	See SBMus Ado	dress Selection ta	ible	1/0

Note: SMBus address is latched on SADR pin

How to Write

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	8 bits	1 bit	8 bits	1 bit	8 bits	1 bit	1 bit
Start bit	Add.	W(0)	Ack	Beginning Byte loca- tion = N	Ack	Data Byte count = X	Ack	Beginning Data Byte (N)	Ack	 Data Byte (N+X-1)	Ack	Stop bit

How to Read

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	8 bits	1 bit
Start bit	Address	W(0)	Ack	Beginning Byte loca- tion = N	Ack	Repeat Start bit	Address	R(1)	Ack	Data Byte count = X	Ack	Beginning Data Byte (N)	Ack

8 bits	1 bit	1 bit
Data Byte	NAck	Ctom hit
 (N+X-1)	INACK	Stop bit





Byte 0: Output Enable Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	Reserved			0		
6	Q3_OE	Q3 output enable	RW	1		
5	Reserved			0		
4	Q2_OE	Q2 output enable	RW	1	Can D11[1.0]	Pin control
3	Q1_OE	Q1 output enable	RW	1	See B11[1:0]	FIII COILLIOI
2	Reserved			0		
1	Q0_OE	Q0 output enable	RW	1		
0	Reserved			0		

Note:

Byte 1: PLL Operating Mode and Output Amplitude Control Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	PLLMODERB1	PLL Mode Readback Bit1	R	Latch	C DII O	: M. J. T.LL.
6	PLLMODERB0	PLL Mode Readback Bit0	R	Latch	See PLL Operat	ing Mode Table
5	PLLMODE_SWCTR	Enable SW control of PLL Mode	RW	0	Values in B1[7:6] set PLL Mode	Values in B1[4:3] set PLL Mode
4	PLLMODE1	PLL Mode control Bit1	RW ⁽¹⁾	0	C DILO	· M 1 77 11
3	PLLMODE0	PLL Mode control Bit0	RW ⁽¹⁾	0	See PLL Operat	ing Mode Table
2	Reserved			1		
1	Amplitude1	Control output amplitude	RW	1	'00' = 0.6V, '01' = 0.68V, '10' =	
0	Amplitude0	Control output amplitude	RW	0	0.75V, '11' = 0.85	5V

Note

1. B1[5] must be set to a 1 for these bits to have any effect on the part

^{1.} A low on these bits will override the OE# pins and force the differential outputs to the state indicated by B11[1:0] (Low/Low default)





Byte 2: Differential Output Slew Rate Control Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	Reserved			1		
6	SLEWRATECTR_Q3	Control slew rate of Q3	RW	1	Slow setting	Fast setting
5	Reserved			1		
4	SLEWRATECTR_Q2	Control slew rate of Q2	RW	1	Slow setting	Fast setting
3	SLEWRATECTR_Q1	Control slew rate of Q1	RW	1	Slow setting	Fast setting
2	Reserved			1		
1	SLEWRATECTR_Q0	Control slew rate of Q0	RW	1	Slow setting	Fast setting
0	Reserved			1		

Byte 3: Frequency Select Control Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	Reserved			1		
6	Reserved			1		
5	FREQ_SEL_EN	Enable SW selection of frequency	RW	0	SW Freq. selection disabled	SW Freq. selection enabled
4	FSEL1	Freq. Select Bit 1	RW ⁽¹⁾	0	0 5	0.1 (77.11
3	FSEL0	Freq. Select Bit 0	RW ⁽¹⁾	0	See Frequency	Select Table
2	Reserved			1		
1	Reserved			1		
0	SLEWRATESEL FB	Adjust Slew Rate of Feedback signal	RW	1	Slow setting	Fast setting

Note

1. B3[5] must be set to a 1 for these bits to have any effect on the part

Byte 4: Reserved

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7:0	Reserved			1		





Byte 5: Revision and Vendor ID Register

Bit	Control Function	Description	Туре	Power Up Condition	0 1	
7	RID3	Revision ID	R	0		
6	RID2		R	0	0000	
5	RID1		R	0	rev = 0000	
4	RID0		R	0		
3	PVID3		R	0		
2	PVID2	W. L. ID	R	0		
1	PVID1	Vendor ID	R	1	Diodes = 0011	
0	PVID0		R	1		

Byte 6: Device Type/Device ID Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1	
7	DTYPE1	D	RW	0	'00' = CG, '01' = ZDB,		
6	DTYPE0	Device type	RW	1	'10' = Reserve, '11' = ZDB		
5	DID5		RW	0	- 000100 binary, 04Hex		
4	DID4		RW	0			
3	DID3		RW	0			
2	DID2	Device ID	RW	1			
1	DID1		RW	0			
0	DID0		RW	0	-		

Byte 7: Reserved

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7:0	Reserved			0x08		

Byte 8 and 9: Reserved

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7:0	Reserved			B8 = 0x36		
7.0	Reserved			B9 = 0x00		





Byte 10: PD Restore

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	Reserved		RW	1		
6	PD Restore	PD Restore to default configuration	RW	1	Clear PD Config	Keep PD Config
5:0	Reserved		R	0		

Byte 11: Stop Control

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	FB_imp[1]	Feedback Zout	RW	0	00=Reserved	10=100 DIF Zout
6	FB_imp[0]		RW	1	01=85 DIF Zout	11 = Reserved
5:2	Reserved			0		
1	STP1	True/ Compliment DIF Output Disable Sate	RW	0	00= Low/Low	10= High/ Low
0	STP0		RW	0	01= HiZ/HiZ	11= Low/High

Byte 12: Impedance Control

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	Q1_Zout1	Q1 Zout	RW			
6	Q1_Zout0	Q1 Zout	RW			
5	Reserved		RW		00 = Reserved	
4	Reserved		RW	0.1	$01 = 85\Omega$	
3	Q0_Zout1	Q0 Zout	RW	01	$10 = 100\Omega$	
2	Q0_Zout0	Q0 Zout	RW		11 = Reserved	
1	Reserved		RW			
0	Reserved		RW			





Byte 13: Impedance Control

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	Reserved		RW			
6	Reserved		RW			
5	Q3_Zout1	Q3 Zout	RW		00 = Reserved	
4	Q3_Zout0	Q3 Zout	RW	01	$01 = 85\Omega$	
3	Reserved		RW	01	$10 = 100\Omega$	
2	Reserved		RW		11 = Reserved	
1	Q2_Zout1	Q2 Zout	RW			
0	Q2_Zout0	Q2 Zout	RW			

Byte 14: OE Termination Control

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	OE1_term1	OE1 Pull up or down	RW	0	00=None	10= Pullup
6	OE1_term0	OE1 Pull up or down	RW	1	01=Pulldown	11=Pullup and Down
5	Reserved		RW	0		
4	Reserved		RW	1		
3	OE0_term1	OE0 Pull up or down	RW	0	00=None	10= Pullup
2	OE0_term0	OE0 Pull up or down	RW	1	01=Pulldown	11=Pullup and Down
1	Reserved			0		
0	Reserved			1		

Byte 15: OE Termination Control

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	Reserved		RW	0		
6	Reserved		RW	1		
5	OE3_term1	OE3 Pull up or down	RW	0	00=None	10= Pullup
4	OE3_term0	OE3 Pull up or down	RW	1	01=Pulldown	11=Pullup and Down
3	Reserved			0		
2	Reserved			1		
1	OE2_term1	OE2 Pull up or down	RW	0	00=None	10= Pullup
0	OE2_term0	OE2 Pull up or down	RW	1	01=Pulldown	11=Pullup and Down

15





Byte 16: Power Good Termination Control

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7:2	Reserved			0x09		
1	PWRGD_PD1		RW	1	00=None	10= Pullup
0	PWRGD_PD0	Clock Power Good and Power Down Pull up or Pull down	RW	0	01=Pulldown	11=Pullup and Down

Byte 17: Reserved

Bit	Control Function	Description	Type	Power Up Condition	0	1
7:0	Reserved			0		

Byte 18: Enable Pin Control

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	Reserved	-	RW	0		
6	OE3_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
5	Reserved			0		
4	OE2_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
3	OE1_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
2	Reserved		RW	0		
1	OE0_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
0	Reserved		RW	0		

Byte 19: Power Down Pin Control

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7:1	Reserved			0		
0	PWRGD_PD	PWRGD_PD Active via Pull up or Pull down	RW	0	Power Down = Low	Power Down = High





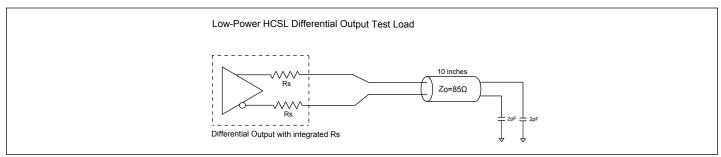


Figure 1. Low Power HCSL Test Circuit

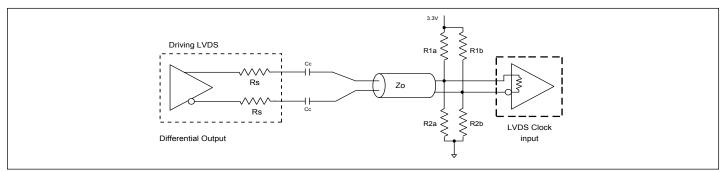


Figure 2. Differential Output Driving LVDS

Alternate Differential Output Terminations ($Z_0 = 85\Omega$)

Component	Receiver with termination	Receiver without termination	Unit
R _{1a} , R _{1b}	10,000	130	Ω
R_{2a} , R_{2b}	5,600	64	Ω
C _C	0.1	0.1	μF
V _{CM}	1.2	1.2	V

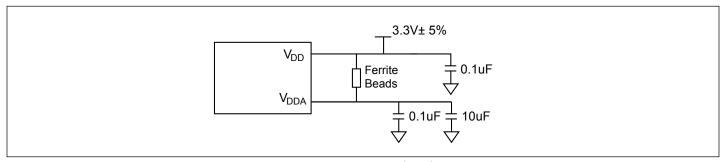


Figure 3. Power Supply Filter





Thermal Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
θ_{JA}	Thermal Resistance Junction to Ambient	Still air			44.7	°C/W
$\theta_{ m JC}$	Thermal Resistance Junction to Case				21.7	°C/W

Part Marking

PI6CB33 402ZHIE $YYWWX\overline{X}$ \bigcirc

YY: Year

WW: Workweek

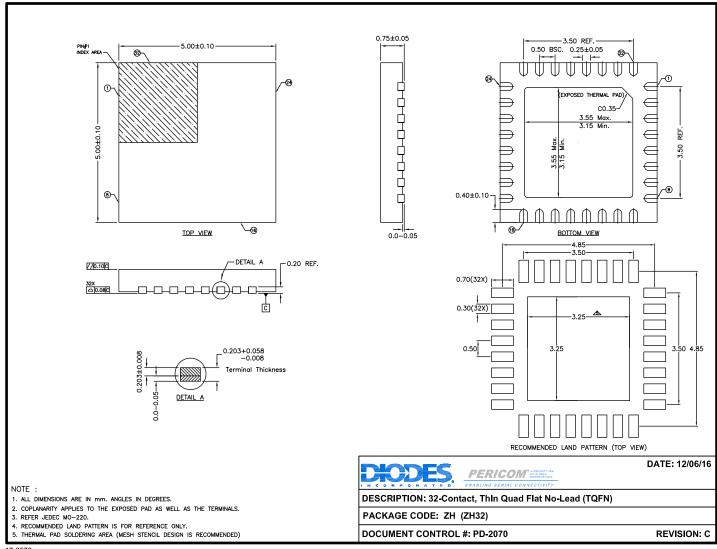
1st X: Assembly Code 2nd X: Fab Code

January 2020





Packaging Mechanical: 32-TQFN (ZH)



For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

Ordering Information

Ordering Code	Package Code	kage Code Package Description	
PI6CB33402ZHIEX	ZH	32-Contact, Thin Quad Flat No-Lead (TQFN)	Top Right Corner
PI6CB33402ZHIEX-13R	ZH	32-Contact, Thin Quad Flat No-Lead (TQFN)	Top Left Corner

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. E = Pb-free and Green
- 5. X suffix = Tape/Reel
- 6. For packaging details, go to our website at: https://www.diodes.com/assets/MediaList-Attachments/Diodes-Package-Information.pdf





IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.

Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
- 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2016, Diodes Incorporated www.diodes.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Clock Buffer category:

Click to view products by Diodes Incorporated manufacturer:

Other Similar products are found below:

MPC962309EJ-1H NB4N121KMNG IDT49FCT805ASO MK2308S-1HILF PL133-27GI-R NB3L02FCT2G NB3L03FCT2G
ZL40200LDG1 ZL40205LDG1 9FG1200DF-1LF 9FG1001BGLF PI49FCT20802QE PI6C10810HE NB7L1008MNG NB7L14MN1G
PI49FCT20807QE PI6C4931502-04LIEX ZL80002QAB1 PI6C4931504-04LIEX PI6C10806BLEX ZL40226LDG1 8T73S208B-01NLGI
SY75578LMG PI49FCT32805QEX PL133-27GC-R MC10LVEP11DG MC10EP11DTG MC100LVEP11DG MC100E111FNG
MC100EP11DTG NB7L14MMNG NB6L14MMNR2G NB6L611MNG NB7V58MMNHTBG NB3N111KMNR4G ADCLK944BCPZ-R7
ZL40217LDG1 NB7LQ572MNG HMC940LC4BTR 9DB801BGLF ADCLK946BCPZ-REEL7 ADCLK946BCPZ ADCLK905BCPZ-R2
ADCLK905BCPZ-R7 ADCLK907BCPZ-R2 ADCLK907BCPZ-WP ADCLK914BCPZ-R2 ADCLK914BCPZ-R7 ADCLK925BCPZ-R2
ADCLK925BCPZ-R7